L Number	Hits	Search Text	DB	Time stamp
13	3	troutman-ronald-roy.in. and diffusion and fabricated	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 12:20
14	2	6157356.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 12:22
15	1	6157356.pn.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/13 12:22
16	1	6157356.pn. and silicon	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/13 12:22
17	3	(organic near3 (electroluminesc$8 EL)) and (drying dry dessicant) and cover and gas and ceramic same (glass silica) and (active adj matrix transistor tft fet) near5 (monocrystalline mono adj crystalline) not single adj crystal	USPAT; US-PGPUB	2003/10/13 12:25
18	3	(organic near3 (electroluminesc$8 EL)) and (drying dry dessicant) and cover and gas and ceramic same (glass silica) and (active adj matrix transistor tft fet) near5 (monocrystalline mono adj crystalline) not single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 12:27
19	3	(organic near3 (electroluminesc$8 EL)) and (drying dry dessicant) and cover and gas and ceramic same (glass silica) and (active adj matrix transistor tft fet) near5 (monocrystalline mono adj crystalline) not single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 12:27
20	0	(organic near3 (electroluminesc$8 EL)) and (drying dry dessicant) and cover and gas with (space gap) and ceramic same (glass silica) and (active adj matrix transistor tft fet) near5 (monocrystalline mono adj crystalline) not single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 12:27
21	3	troutman-ronald-roy.in. and diffusion and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 13:41
22	2	troutman-ronald-roy.in. and diffusion and silicon and well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 12:49
23	2	troutman-ronald-roy.in. and diffusion and silicon and (well body)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 13:40
24	2143	(313/500,504,505,512).CCLS.	USPAT; US-PGPUB	2003/10/13 13:41
25	1201	(445/24).CCLS.	USPAT; US-PGPUB	2003/10/13 13:41
26	611	(345/36,76).CCLS.	USPAT; US-PGPUB	2003/10/13 13:41
-	229	(445/25).CCLS.	USPAT	2002/08/28 14:30
-	343	(313/512).CCLS.	USPAT	2002/08/28 14:39
-	0	09671654.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 14:39

-	1	09671654.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 14:39
-	229	(445/25).CCLS.	USPAT	2002/08/28 14:48
-	722	((313/512) or (445/25)).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 14:48
-	17	(((313/512) or (445/25)).CCLS.) and active adj matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 14:55
-	13	((((313/512) or (445/25)).CCLS.) and active adj matrix) and crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 14:56
-	1	((((313/512) or (445/25)).CCLS.) and active adj matrix) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 14:58
-	3	5672083.URPN.	USPAT	2002/08/28 14:57
-	1	((((313/512) or (445/25)).CCLS.) and active adj matrix) and (field adj effect adj transistor FET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:01
-	0	(257.$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:01
-	134751	(257/$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:02
-	66945	(313/$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:02
-	8	((257/$).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:04
-	5	((257/$).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:32
-	0	((313/$).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:25
-	4347	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 16:14

-	2	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:36
-	4396	yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/12 13:14
-	4178	yamazaki-shunpei.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:31
-	943	yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT	2003/06/11 18:06
-	1171	yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT; US-PGPUB	2003/10/03 20:15
-	0	(yamazaki-shunpei.in. or arai-yasuyuki.in.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:33
-	1	(yamazaki-shunpei.in. or arai-yasuyuki.in.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:33
-	3	1089595.URPN.	USPAT	2002/08/28 15:35
-	2	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET mostft) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 16:15
-	5136	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 13:56
-	2	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET mostft) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 16:15
-	2	("6153893" | "6246070").PN.	USPAT	2002/08/28 16:27
-	5150	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:00
-	3	("6351010").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 07:37
-	2	("6153893" | "6246070").PN.	USPAT	2002/08/29 07:47
-	0	(("6153893" | "6246070").PN.) and organic with (EL electroluminescence electroluminescent)	USPAT	2002/08/29 07:46
-	0	(("6153893" | "6246070").PN.) and organic same (EL electroluminescence electroluminescent)	USPAT	2002/08/29 07:46
-	3	semiconductor-energy-laboratory.as.	USPAT	2002/08/29 07:48

-	4	semiconductor-energy-laboratory.as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 07:51
-	7	sony.as. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 07:55
-	3	sony.as. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor) and (organic with (EL electroluminescent electroluminescence))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:00
-	0	sony.as. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor) and (organic with (EL electroluminescent electroluminescence)) and inert	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:00
-	2	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:38
-	2	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:43
-	8	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:44
-	8	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and gas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:44
-	5	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (inert adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:17
-	80	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and TFT with FET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:25
-	1	6274887.URPN.	USPAT	2002/08/29 09:55
-	14	("5247190" | "5399502" | "5401982" | "5576556" | "5612234" | "5620905" | "5643826" | "5710606" | "5719065" | "5736414" | "5789762" | "5923962" | "5926735" | "5959313").PN.	USPAT	2002/08/29 09:56

-	0	(("5247190" | "5399502" | "5401982" | "5576556" | "5612234" | "5620905" | "5643826" | "5710606" | "5719065" | "5736414" | "5789762" | "5923962" | "5926735" | "5959313").PN.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (inert adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:59
-	0	(("5247190" | "5399502" | "5401982" | "5576556" | "5612234" | "5620905" | "5643826" | "5710606" | "5719065" | "5736414" | "5789762" | "5923962" | "5926735" | "5959313").PN.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate and single adj crystal and (inert adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:59
-	492	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and inert gas with organic adj EL	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:02
-	9	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and inert adj gas with organic adj EL	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:02
-	0	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and inert adj gas with organic adj EL same oxidize	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:03
-	0	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and inert adj gas same organic adj EL same (oxidize deteriorate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:03
-	0	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (rare adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:20
-	8	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen ni)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:21
-	3	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen ni)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:24

-	3	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:12
-	3	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium he argon ar krypton kr xenon xe nitrogen ni)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:26
-	3	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium he argon ar krypton kr xenon xe nitrogen n)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:27
-	1	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium he argon ar krypton kr xenon xe nitrogen n) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:28
-	1	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen ni)) and (helium he argon ar krypton kr xenon xe nitrogen n) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:28
-	1	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen ni)) and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas inert adj gas) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:29

-	1	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen ni)) and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:14
-	4	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:20
-	1	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:15
-	4	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 14:12
-	1075	313/504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:58
-	0	313/504,500	USPAT; US-PGPUB	2002/08/29 11:58
-	1650	313/504 313/500	USPAT; US-PGPUB	2002/08/29 12:20
-	1075	313/504	USPAT; US-PGPUB	2002/08/29 12:21
-	1064	((313/504) or (313/500)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:36
-	116	(((313/504) or (313/500)).CCLS.) AND Active adj matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:21
-	114	((((313/504) or (313/500)).CCLS.) AND Active adj matrix) and (field effect transistor fet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:23
-	9	(((((313/504) or (313/500)).CCLS.) AND Active adj matrix) and (field effect transistor fet)) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 13:32

-	7	((((((313/504) or (313/500)).CCLS.) AND Active adj matrix) and (field effect transistor fet)) and single adj crystal) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:28
-	7	((((((313/504) or (313/500)).CCLS.) AND Active adj matrix) and (field effect transistor fet)) and single adj crystal) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:36
-	0	20020074938.URPN.	USPAT	2002/08/29 12:35
-	810	(((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:37
-	530	(((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen n) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:38
-	407	(((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:39
-	2	(((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (envelope vacant vacancy) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:40
-	181	(((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) and (organic adj EL organic adj layer) and (barium adj oxide silica gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:41
-	57	(((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica gel) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:44
-	615	(((313/504) or (313/500)).CCLS.) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:44
-	57	((((313/504) or (313/500)).CCLS.) and (organic adj EL organic adj layer)) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:45
-	57	((((313/504) or (313/500)).CCLS.) and (organic adj EL organic adj layer)) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:47
-	48	((((313/504) or (313/500)).CCLS.) and (organic adj EL organic adj layer)) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 13:33
-	10	(((((313/504) or (313/500)).CCLS.) AND Active adj matrix) and (field effect transistor fet)) and (single adj crystal monocrystal monocrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 13:32

-	0	((((((313/504) or (313/500)).CCLS.) AND Active adj matrix) and (field effect transistor fet)) and (single adj crystal monocrystal monocrystalline)) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica adj gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 13:53
-	3	(((((313/504) or (313/500)).CCLS.) AND Active adj matrix) and (field effect transistor fet)) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica adj gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 13:54
-	7008	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 13:57
-	0	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and active adj matrix and (FET field adj effect adj transistor) same organic adj EL and (barium adj oxide silica gel) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:00
-	1	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and active adj matrix and (FET field adj effect adj transistor) and organic adj EL and (barium adj oxide silica adj gel) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:01
-	1	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence) and (barium adj oxide silica adj gel) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:03
-	1	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence) and (barium adj oxide silica adj gel) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:03
-	1	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence) and (barium adj oxide silica adj gel) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB	2002/08/29 14:23
-	2	("6175186").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:04

-	24	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:06
-	10	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:27
-	1	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) and goggle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:35
-	1	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence) and (barium adj oxide silica adj gel)	USPAT; US-PGPUB	2002/08/29 14:23
-	1	jp10285476	JPO	2002/08/29 14:24
-	15	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:53
-	537	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) and (barium oxide silica adj gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:36
-	11	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) and (barium oxide silica adj gel) and goggle	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:41
-	0	jp10333665	JPO	2002/08/29 14:42
-	0	semiconductor adj laboratory and yamazaki and "1998"	JPO	2002/08/29 14:43
-	5179	yamazaki and "1998"	JPO	2002/08/29 14:43
-	0	yamazaki and "1998" and semiconductor adj energy adj laboratory	JPO	2002/08/29 14:43
-	0	10-333665 and yamazaki	JPO	2002/08/29 14:48

L-	0	"1333665" and yamazaki	JPO	2002/08/29 14:48
L-	0	"10333665" and yamazaki	JPO	2002/08/29 14:48
L-	0	"jp10333665" and yamazaki	JPO	2002/08/29 14:48
L-	0	"jp410333665" and yamazaki	JPO	2002/08/29 14:48
L-	0	"jp310333665" and yamazaki	JPO	2002/08/29 14:48
L-	0	"jp310333665"	JPO	2002/08/29 14:48
L-	0	"jp410333665"	JPO	2002/08/29 14:48
L-	0	"jp10333665"	JPO	2002/08/29 14:48
L-	368	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) and (barium oxide silica adj gel)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:50
L-	83	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) and (barium adj oxide silica adj gel)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:51
L-	36	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) same (barium adj oxide silica adj gel)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:52
L-	3	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) same (barium adj oxide)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:55
L-	7	("5739545" | "5747930" | "5834894" | "6037718" | "6046543" | "6246179" | "6307324").PN.	USPAT	2002/08/29 14:54
L-	2	("6175186").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:13
L-	0	(313/$ and ceramic with transparent).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:27
L-	0	(313/$ and ceramic same transparent).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:27
L-	0	(313/$ and ceramic same clear).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:27
L-	66966	("313").CLAS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:27

-	0	((313/$).CCLS.) and nitride adj ceramic with (clear transparent transparency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:28
-	359	((313/$).CCLS.) and ceramic with (clear transparent transparency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 16:50
-	0	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and active adj matrix with goggle	USPAT	2002/08/29 15:54
-	24	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and display with goggle	USPAT	2002/08/29 15:59
-	0	jp10361563	JPO	2002/08/29 15:58
-	0	jp010361563	JPO	2002/08/29 15:58
-	25	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and display same goggle	USPAT	2002/08/29 15:59
-	26	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and display and goggle	USPAT	2002/08/29 16:46
-	9	nitride adj ceramic with (transparent clear)	USPAT	2002/08/29 16:47
-	0	nitride adj ceramic with oxide with glass with (transparent clear)	USPAT	2002/08/29 16:47
-	28	((313/$).CCLS.) and nitride adj ceramic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 16:52
-	0	((313/$).CCLS.) and nitride adj ceramic same (transparent clear)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 16:51
-	20	((313/$).CCLS.) and nitride with ceramic same (display clear transparent transparency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 17:07
-	0	jp102854476	JPO	2002/08/29 17:07
-	0	jp12854476	JPO	2002/08/29 17:07
-	0	jp0102854476	JPO	2002/08/29 17:12
-	3	("6351010").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 17:13
-	0	("1459 and yamanaka and insulated adj gate").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 17:13
-	8	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and yamanaka and insulated adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 17:16

-	0	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and insulated adj gate and organic adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 17:17
-	3	sony.as. and insulated adj gate adj field and organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 17:18
-	389	yamazaki-shunpei.in. or arai-yasuyuki.in.	US-PGPUB	2003/06/11 18:07
-	22	yamazaki-shunpei.in. and arai-yasuyuki.in.	US-PGPUB	2003/06/11 18:07
-	21	yamazaki-shunpei.in. and arai-yasuyuki.in. and organic	US-PGPUB	2003/06/12 11:17
-	9	"passivation film 847"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:56
-	0	"passivation film 847 is formed on the anode layer 846"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 11:01
-	0	"passivation film 847 is formed on the anode layer 846."	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:57
-	1420	semiconductor adj device adj method adj fabricating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 11:00
-	745	semiconductor adj device adj method adj fabricating.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 11:01
-	0	"passivation film 847 is formed"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 11:02
-	0	yamazaki-shunpei.in. and arai-yasuyuki.in. and muakami-satoshi.in.	US-PGPUB	2003/06/12 11:18
-	1	yamazaki-shunpei.in. and arai-yasuyuki.in. and murakami-satoshi.in.	US-PGPUB	2003/06/12 11:18
-	2171	((313/512) or (313/504) or (313/500) or (445/24)).CCLS.	USPAT	2003/06/12 15:58
-	237	(OLED organic adj3 el adj3 (device display)).bi. and (fET field adj effect adj transistor).bi.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:07
-	315	(OLED organic adj3 el adj3 (device display) organic adj2 (electroluminescent electroluminescence)).bi. and (fET field adj effect adj transistor).bi.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:08
-	166	(OLED organic adj3 el adj3 (device display) organic adj2 (electroluminescent electroluminescence)).bi. and (fET field adj effect adj transistor).bi.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:08
-	98	((OLED organic adj3 el adj3 (device display) organic adj2 (electroluminescent electroluminescence)).bi. and (fET field adj effect adj transistor).bi.) and (matrix matrices)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:09

-	52	(((OLED organic adj3 el adj3 (device display) organic adj2 (electroluminescent electroluminescence)).bi. and (fET field adj effect adj transistor).bi.) and (matrix matrices)) and (gas nitrogen krypton xenon argon neon helium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:16
-	36	(((OLED organic adj3 el adj3 (device display) organic adj2 (electroluminescent electroluminescence)).bi. and (fET field adj effect adj transistor).bi.) and (matrix matrices)) and (gas nitrogen krypton xenon argon neon helium) and (dry drying desiccant getter)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:27
-	36	(US-6221553-$ or US-6219113-$ or US-6214520-$ or US-6194119-$ or US-6157127-$ or US-6140009-$ or US-6114088-$ or US-6103558-$ or US-5935720-$ or US-5908581-$ or US-5677546-$ or US-5449582-$ or US-6284425-$ or US-6270944-$ or US-6242152-$ or US-6228555-$ or US-6410201-$ or US-6403809-$ or US-6372558-$ or US-6358664-$ or US-6351010-$ or US-6346718-$ or US-6291126-$ or US-6291116-$ or US-6521525-$ or US-6518594-$).did. or (US-6504215-$ or US-6503831-$ or US-6492190-$ or US-6482564-$ or US-6468715-$ or US-6429584-$ or US-5405724-$).did. or (EP-1089595-$).did. or (JP-2001167877-$).did. or (EP-1089595-$).did.	USPAT; EPO; JPO; DERWENT	2003/06/12 16:18
-	10	((US-6221553-$ or US-6219113-$ or US-6214520-$ or US-6194119-$ or US-6157127-$ or US-6140009-$ or US-6114088-$ or US-6103558-$ or US-5935720-$ or US-5908581-$ or US-5677546-$ or US-5449582-$ or US-6284425-$ or US-6270944-$ or US-6242152-$ or US-6228555-$ or US-6410201-$ or US-6403809-$ or US-6372558-$ or US-6358664-$ or US-6351010-$ or US-6346718-$ or US-6291126-$ or US-6291116-$ or US-6521525-$ or US-6518594-$).did. or (US-6504215-$ or US-6503831-$ or US-6492190-$ or US-6482564-$ or US-6468715-$ or US-6429584-$ or US-5405724-$).did. or (EP-1089595-$).did. or (JP-2001167877-$).did. or (EP-1089595-$).did.) and (silicon si) adj4 substrate	USPAT; EPO; JPO; DERWENT	2003/06/12 16:19

-	10	((US-6221553-$ or US-6219113-$ or US-6214520-$ or US-6194119-$ or US-6157127-$ or US-6140009-$ or US-6114088-$ or US-6103558-$ or US-5935720-$ or US-5908581-$ or US-5677546-$ or US-5449582-$ or US-6284425-$ or US-6270944-$ or US-6242152-$ or US-6228555-$ or US-6410201-$ or US-6403809-$ or US-6372558-$ or US-6358664-$ or US-6351010-$ or US-6346718-$ or US-6291126-$ or US-6291116-$ or US-6521525-$ or US-6518594-$).did. or (US-6504215-$ or US-6503831-$ or US-6492190-$ or US-6482564-$ or US-6468715-$ or US-6429584-$ or US-5405724-$).did. or (EP-1089595-$).did. or (JP-2001167877-$).did. or (EP-1089595-$).did.) and (silicon si) adj4 substrate	USPAT; EPO; JPO; DERWENT	2003/06/12 16:51
-	2	(((US-6221553-$ or US-6219113-$ or US-6214520-$ or US-6194119-$ or US-6157127-$ or US-6140009-$ or US-6114088-$ or US-6103558-$ or US-5935720-$ or US-5908581-$ or US-5677546-$ or US-5449582-$ or US-6284425-$ or US-6270944-$ or US-6242152-$ or US-6228555-$ or US-6410201-$ or US-6403809-$ or US-6372558-$ or US-6358664-$ or US-6351010-$ or US-6346718-$ or US-6291126-$ or US-6291116-$ or US-6521525-$ or US-6518594-$).did. or (US-6504215-$ or US-6503831-$ or US-6492190-$ or US-6482564-$ or US-6468715-$ or US-6429584-$ or US-5405724-$).did. or (EP-1089595-$).did. or (JP-2001167877-$).did. or (EP-1089595-$).did.) and (silicon si) adj4 substrate) and (gas nitrogen krypton xenon argon neon helium).clm.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 19:01
-	2	6103558.pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:44
-	1	6103558.pn.	USPAT; EPO; JPO; IBM_TDB	2003/06/12 17:56
-	36	((US-6221553-$ or US-6219113-$ or US-6214520-$ or US-6194119-$ or US-6157127-$ or US-6140009-$ or US-6114088-$ or US-6103558-$ or US-5935720-$ or US-5908581-$ or US-5677546-$ or US-5449582-$ or US-6284425-$ or US-6270944-$ or US-6242152-$ or US-6228555-$ or US-6410201-$ or US-6403809-$ or US-6372558-$ or US-6358664-$ or US-6351010-$ or US-6346718-$ or US-6291126-$ or US-6291116-$ or US-6521525-$ or US-6518594-$).did. or (US-6504215-$ or US-6503831-$ or US-6492190-$ or US-6482564-$ or US-6468715-$ or US-6429584-$ or US-5405724-$).did. or (EP-1089595-$).did. or (JP-2001167877-$).did. or (EP-1089595-$).did.) and organic with (el electroluminescent electroluminescence)	USPAT; EPO; JPO; DERWENT	2003/06/12 16:52

10 (((US-6221553-$ or US-6219113-$ or
US-6214520-$ or US-6194119-$ or
US-6157127-$ or US-6140009-$ or
US-6114088-$ or US-6103558-$ or
US-5935720-$ or US-5908581-$ or
US-5677546-$ or US-5449582-$ or
US-6284425-$ or US-6270944-$ or
US-6242152-$ or US-6228555-$ or
US-6410201-$ or US-6403809-$ or
US-6372558-$ or US-6358664-$ or
US-6351010-$ or US-6346718-$ or
US-6291126-$ or US-6291116-$ or
US-6521525-$ or US-6518594-$).did. or
(US-6504215-$ or US-6503831-$ or
US-6492190-$ or US-6482564-$ or
US-6468715-$ or US-6429584-$ or
US-5405724-$).did. or (EP-1089595-$).did.
or (JP-2001167877-$).did. or